

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>		
			Application Number	10/698,501	
			Filing Date	October 31, 2003	
			First Named Inventor	Heon Lee	
			Art Unit	2824	
			Examiner Name	Son T. Dinh	
Sheet	<b>C1</b>	of	<b>C1</b>	Attorney Docket Number	5649-2226

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	1	US- 2003/0198113 A1	10-23-2003	Abraham et al.	
	2	US- 2003/0123282 A1	07-03-2003	Nickel et al.	
	3	US- 6,535,416 B1	03-18-2003	Daughton et al.	
	4	US- 2003/0073398 A1	01-09-2003	Daughton et al.	
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Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code, Number, Kind Code (if known)				
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	7	DE 10 2004 022 573 A1	04-07-2005	Hewlett Packard Development Co.		T
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	12	JP 04-023293 A	01-27-1992	Toshiba Corp.		T

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T
	13	Beech et al., "Curie point written magnetoresistive memory," Journal of Applied Physics, Vol. 87, No. 9, May 1, 2000, pp. 6403-6405			
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Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.